

isc Silicon NPN RF Transistor

2SC3512

DESCRIPTION

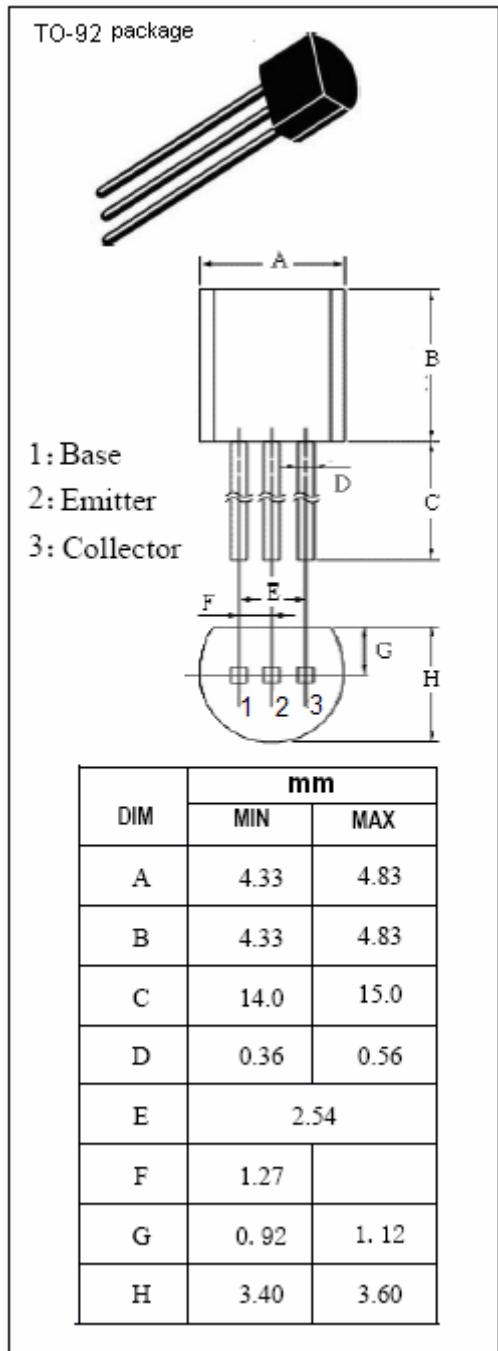
- Low Noise and High Gain
 NF = 1.6 dB TYP. @f = 900 MHz
 PG = 10.5 dB TYP. @f = 900 MHz

APPLICATIONS

- Designed for use in low-noise and small signal amplifiers from VHF ~ UHF band.

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	15	V
V _{CEO}	Collector-Emitter Voltage	11	V
V _{EBO}	Emitter-Base Voltage	2	V
I _C	Collector Current-Continuous	50	mA
P _C	Collector Power Dissipation @T _C =25°C	0.6	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



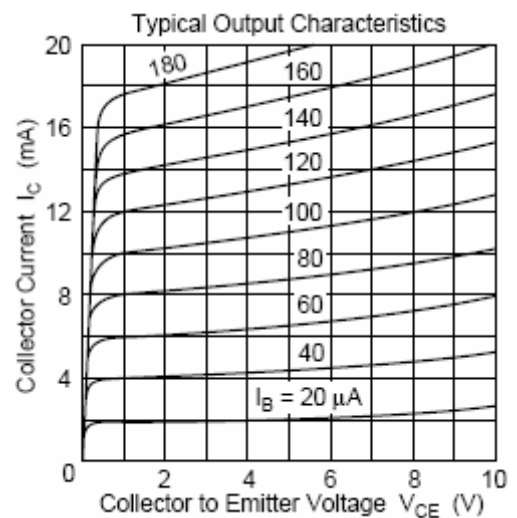
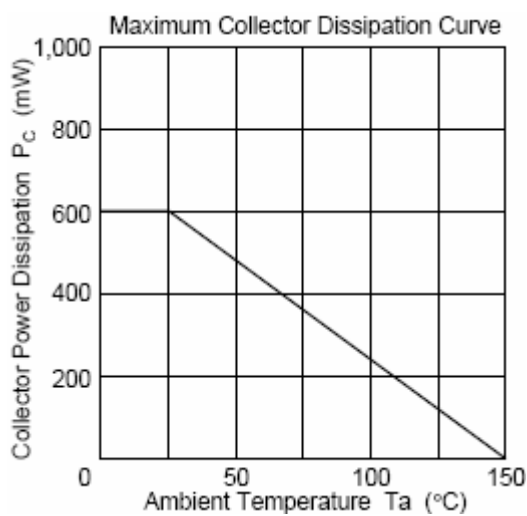
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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 10 μ A ; I _E = 0	15			V
I _{CBO}	Collector Cutoff Current	V _{CB} = 12V; I _E = 0			1.0	μ A
I _{CEO}	Collector Cutoff Current	V _{CE} = 10V; R _{BE} = ∞			1.0	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 1V; I _C = 0			1.0	μ A
h _{FE}	DC Current Gain	I _C = 20mA ; V _{CE} = 5V	50		250	
f _T	Current-Gain—Bandwidth Product	I _C = 20mA ; V _{CE} = 5V		6.0		GHz
C _{OB}	Output Capacitance	I _E = 0 ; V _{CB} = 5V; f= 1.0MHz		1.2	1.6	pF
PG	Power Gain	I _C = 20mA; V _{CE} = 5V; f= 900MHz		10.5		dB
NF	Noise Figure	I _C = 5mA ; V _{CE} = 5V; f= 900MHz		1.6		dB



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